

## EE247 Lecture 6

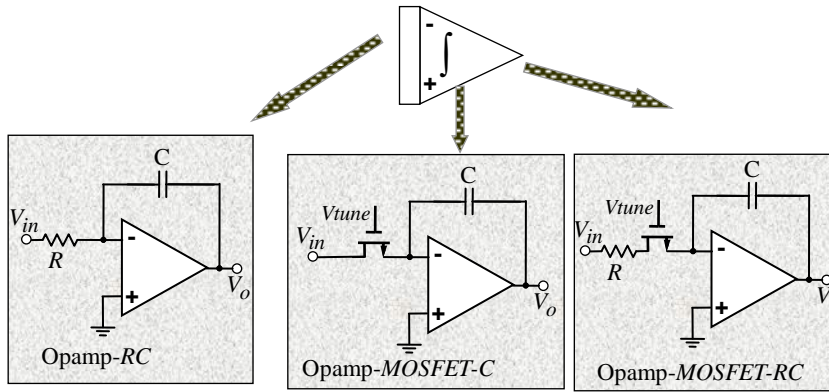
- Continuous-time filters (continued)
  - Opamp MOSFET-C filters
  - Opamp MOSFET-RC filters
  - Gm-C filters
- Frequency tuning for continuous-time filters
  - Trimming via fuses or laser
  - Automatic on-chip filter tuning
    - Continuous tuning
      - Master-slave tuning
    - Periodic off-line tuning
      - Systems where filter is followed by ADC & DSP, existing hardware can be used to periodically update filter freq. response

## Summary Lecture 5

- Continuous-time filters
  - Effect of integrator non-idealities on integrated continuous-time filter behavior
    - Effect of integrator finite DC gain & non-dominant poles on filter frequency response
    - Integrator non-linearities affecting filter maximum signal handling capability (harmonic distortion and intermodulation distortion)
    - Effect of integrator component variations and mismatch on filter response & need for frequency tuning
- Frequency tuning for continuous-time filters
  - Frequency adjustment by making provisions to have variable R or C
- Various integrator topologies used in filters
  - Opamp MOSFET-C filters (to be continued)

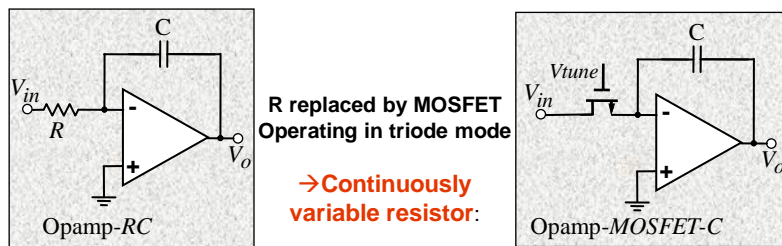
## Integrator Implementation

### Opamp-RC & Opamp-MOSFET-C & Opamp-MOSFET-RC

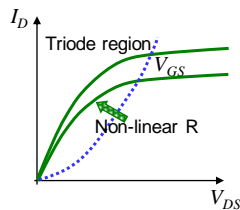


$$\frac{V_o}{V_{in}} = \frac{-\omega_o}{s} \quad \text{where} \quad \omega_o = \frac{1}{R_{eq}C}$$

## Use of MOSFETs as Variable Resistors



MOSFET IV characteristic:

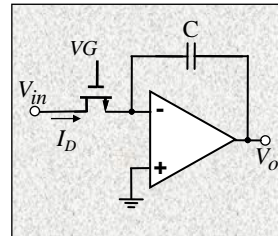


## Opamp MOSFET-C Integrator Single-Ended Integrator

$$I_D = \mu C_{ox} \frac{W}{L} \left[ (V_{gs} - V_{th}) V_{ds} - \frac{V_{ds}^2}{2} \right]$$

$$I_D = \mu C_{ox} \frac{W}{L} \left[ (V_{gs} - V_{th}) V_i - \frac{V_i^2}{2} \right]$$

$$G = \frac{\partial I_D}{\partial V_i} = \mu C_{ox} \frac{W}{L} (V_{gs} - V_{th} - V_i)$$



→ Tunable by varying VG:

By varying VG effective admittance is tuned  
→ Tunable integrator time constant

**Problem: Single-ended MOSFET-C Integrator** → Effective R non-linear  
Note that the non-linearity is mainly 2<sup>nd</sup> order type

## Use of MOSFETs as Resistors Differential Integrator

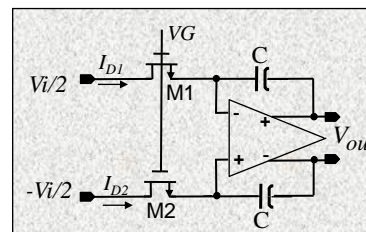
$$I_D = \mu C_{ox} \frac{W}{L} \left( V_{gs} - V_{th} - \frac{V_{ds}}{2} \right) V_{ds}$$

$$I_{D1} = \mu C_{ox} \frac{W}{L} \left( V_{gs} - V_{th} - \frac{V_i}{4} \right) \frac{V_i}{2}$$

$$I_{D2} = -\mu C_{ox} \frac{W}{L} \left( V_{gs} - V_{th} + \frac{V_i}{4} \right) \frac{V_i}{2}$$

$$I_{D1} - I_{D2} = \mu C_{ox} \frac{W}{L} (V_{gs} - V_{th}) V_i$$

$$G = \frac{\partial (I_{D1} - I_{D2})}{\partial V_i} = \mu C_{ox} \frac{W}{L} (V_{gs} - V_{th})$$



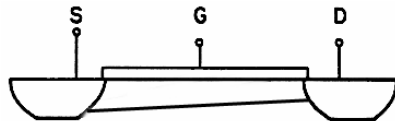
Opamp-MOSFET-C

- Non-linear term is of even order & cancelled!
- Admittance independent of Vi

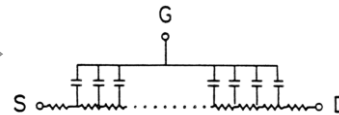
**Problem: Threshold voltage dependence**

## Use of MOSFET as Resistor Issues

MOS xtor operating in triode region  
Cross section view



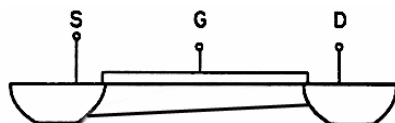
Distributed channel resistance & gate capacitance



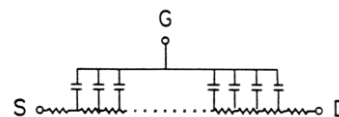
- Distributed nature of gate capacitance & channel resistance results in infinite no. of high-frequency poles:
  - Excess phase @ the unity-gain frequency of the integrator
  - Enhanced integrator Q
  - Enhanced filter Q,
  - Peaking in the filter passband

## Use of MOSFET as Resistor Issues

MOS xtor operating in triode region  
Cross section view



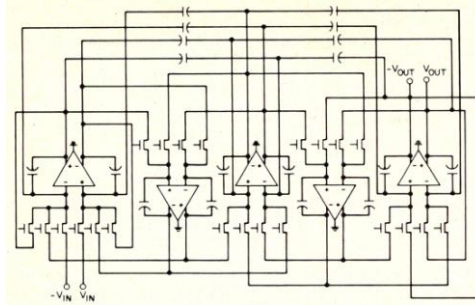
Distributed channel resistance & gate capacitance



- Tradeoffs affecting the choice of device channel length:
  - Filter performance mandates well-matched MOSFETs → long channel devices desirable
  - Excess phase increases with  $L^2$  → Q enhancement and potential for oscillation!
    - Tradeoff between device matching and integrator Q
    - This type of filter limited to low frequencies

## Example: Opamp MOSFET-C Filter

- Suitable for low frequency applications
- Issues with linearity
- Linearity achieved ~40-50dB
- Needs tuning
- Continuously tunable



5<sup>th</sup> Order Elliptic MOSFET-C LPF  
with 4kHz Bandwidth

Ref: Y. Tsvividis, M.Banu, and J. Khoury, "Continuous-Time MOSFET-C Filters in VLSI", *IEEE Journal of Solid State Circuits* Vol. SC-21, No.1 Feb. 1986, pp. 15-30

## Improved MOSFET-C Integrator

$$I_D = \mu C_{ox} \frac{W}{L} \left( V_{gs} - V_{th} - \frac{V_{ds}}{2} \right) V_{ds}$$

$$I_{D1} = \mu C_{ox} \frac{W}{L} \left( V_{gs1} - V_{th} - \frac{V_i}{4} \right) \frac{V_i}{2}$$

$$I_{D3} = -\mu C_{ox} \frac{W}{L} \left( V_{gs3} - V_{th} + \frac{V_i}{4} \right) \frac{V_i}{2}$$

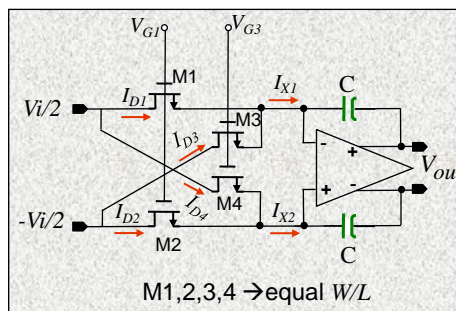
$$I_{X1} = I_{D1} + I_{D3}$$

$$= \mu C_{ox} \frac{W}{L} \left( V_{gs1} - V_{gs3} - \frac{V_i}{2} \right) \frac{V_i}{2}$$

$$I_{X2} = \mu C_{ox} \frac{W}{L} \left( V_{gs3} - V_{gs1} - \frac{V_i}{2} \right) \frac{V_i}{2}$$

$$I_{X1} - I_{X2} = \mu C_{ox} \frac{W}{L} (V_{gs1} - V_{gs3}) V_i$$

$$G = \frac{\partial (I_{X1} - I_{X2})}{\partial V_i} = \mu C_{ox} \frac{W}{L} (V_{gs1} - V_{gs3})$$

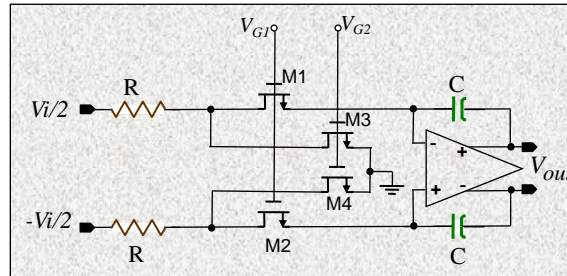


**No threshold voltage dependence**

**Linearity achieved in the order of 50-70dB**

Ref: Z. Czarnul, "Modification of the Banu-Tsvividis Continuous-Time Integrator Structure," *IEEE Transactions on Circuits and Systems*, Vol. CAS-33, No. 7, pp. 714-716, July 1986.

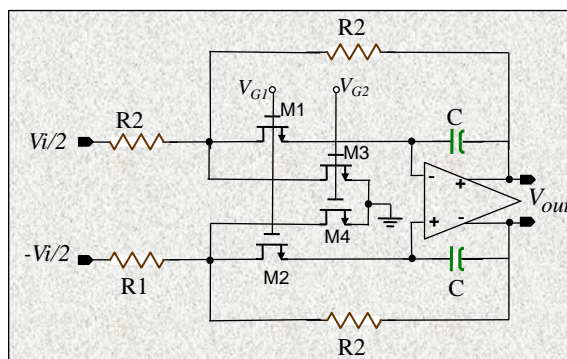
## R-MOSFET-C Integrator



- Improvement over MOSFET-C by adding resistor in series with MOSFET
- Voltage drop primarily across fixed resistor → small MOSFET  $V_{ds}$  → improved linearity & reduced tuning range
- Generally low frequency & low Q applications

Ref: U-K Moon, and B-S Song, "Design of a Low-Distortion 22-kHz Fifth Order Bessel Filter," *IEEE Journal of Solid State Circuits*, Vol. 28, No. 12, pp. 1254-1264, Dec. 1993.

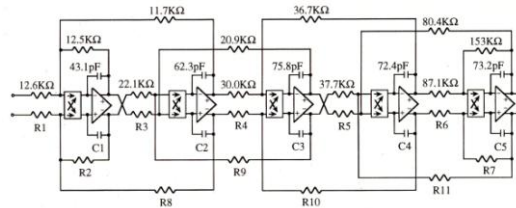
## R-MOSFET-C Lossy Integrator



- Negative feedback around the non-linear MOSFETs improves linearity but compromises frequency response accuracy

Ref: U-K Moon, and B-S Song, "Design of a Low-Distortion 22-kHz Fifth Order Bessel Filter," *IEEE Journal of Solid State Circuits*, Vol. 28, No. 12, pp. 1254-1264, Dec. 1993.

## Example: Opamp MOSFET-RC Filter



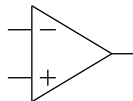
**5<sup>th</sup> Order Bessel MOSFET-RC LPF 22kHz bandwidth  
THD  $\rightarrow$  -90dB for 4Vp-p, 2kHz input signal**

- Suitable for low frequency, low Q applications
- Significant improvement in linearity compared to MOSFET-C
- Needs tuning

Ref: U-K Moon, and B-S Song, "Design of a Low-Distortion 22-kHz Fifth Order Bessel Filter," *IEEE Journal of Solid State Circuits*, Vol. 28, No. 12, pp. 1254-1264, Dec. 1993.

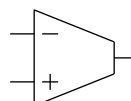
## Operational Amplifiers (Opamps) versus Operational Transconductance Amplifiers (OTA)

**Opamp**  
Voltage controlled  
voltage source



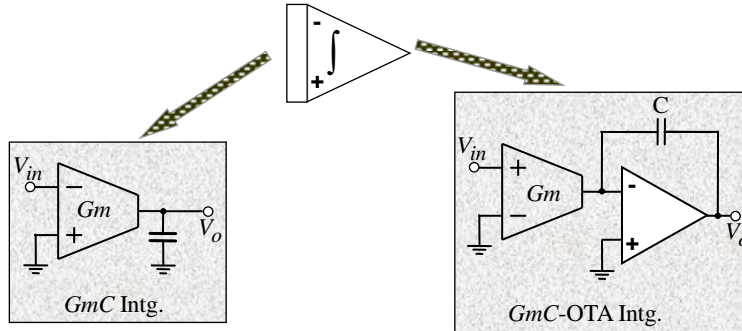
- Output in the form of voltage
- Low output impedance
- Can drive R-loads
- Good for RC filters, OK for SC filters
- Extra buffer adds complexity, power dissipation

**OTA**  
Voltage controlled  
current source



- Output in the form of current
- High output impedance
- In the context of filter design called *gm-cells*
- Cannot drive R-loads
- Good for SC & gm-C filters
- Typically, less complex compared to opamp  $\rightarrow$  higher freq. potential
- Typically lower power

## Integrator Implementation Transconductance-C & Opamp-Transconductance-C



$$\frac{V_o}{V_{in}} = \frac{-\omega_o}{s} \quad \text{where} \quad \omega_o = \frac{G_m}{C}$$

## Gm-C Filters Simplest Form of CMOS Gm-C Integrator

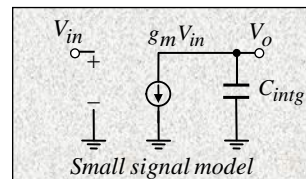
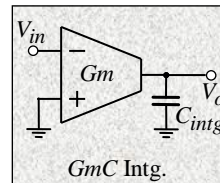
- Use small signal model to derive transfer function:

$$V_o = -g_m \times V_{in} \times C_{int} g s$$

$$\frac{V_o}{V_{in}} = -\frac{g_m}{C_{int} g s}$$

$$\frac{V_o}{V_{in}} = \frac{-\omega_o}{s}$$

$$\rightarrow \omega_o = \frac{g_m}{C_{int} g s}$$



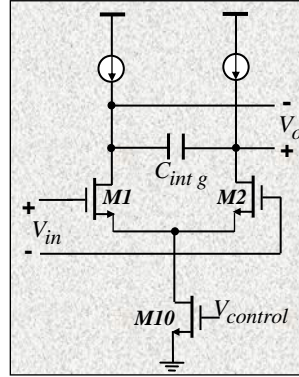
- Issue: Design is parasitic sensitive



## Gm-C Filters

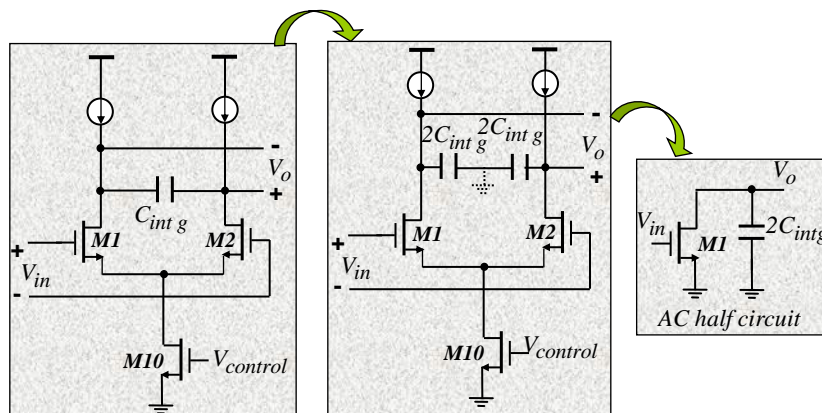
### Simplest Form of CMOS Gm-C Integrator

- Transconductance element formed by the source-coupled pair  $M1$  &  $M2$
- All MOSFETs operating in saturation region
- Current in  $M1$  &  $M2$  can be varied by changing  $V_{control}$
- Find transfer function by drawing ac small-signal half circuit



Ref: H. Khorramabadi and P.R. Gray, "High Frequency CMOS continuous-time filters," IEEE Journal of Solid-State Circuits, Vol.-SC-19, No. 6, pp.939-948, Dec. 1984.

### Simplest Form of CMOS Gm-C Integrator AC Half Circuit



## Gm-C Filters

### Simplest Form of CMOS Gm-C Integrator

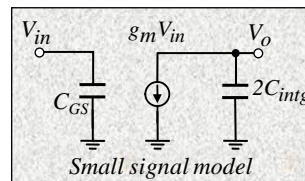
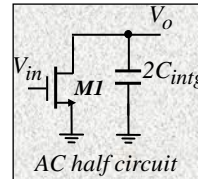
- Use ac half circuit & small signal model to derive transfer function:

$$V_o = -g_m^{M1,2} \times V_{in} \times 2C_{int} g s$$

$$\frac{V_o}{V_{in}} = -\frac{g_m^{M1,2}}{2C_{int} g s}$$

$$\frac{V_o}{V_{in}} = \frac{-\omega_o}{s}$$

$$\rightarrow \omega_o = \frac{g_m^{M1,2}}{2 \times C_{int} g}$$



## Gm-C Filters

### Simplest Form of CMOS Gm-C Integrator

- MOSFET in saturation region:

$$I_d = \frac{\mu C_{ox} W}{2 L} (V_{gs} - V_{th})^2$$

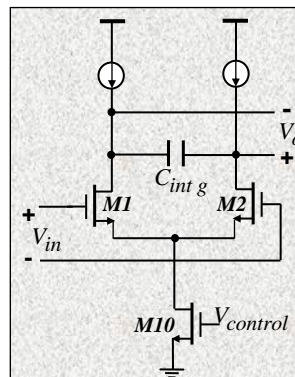
- Gm is given by:

$$g_m^{M1 \& M2} = \frac{\partial I_d}{\partial V_{gs}} = \mu C_{ox} \frac{W}{L} (V_{gs} - V_{th})$$

$$= 2 \frac{I_d}{(V_{gs} - V_{th})}$$

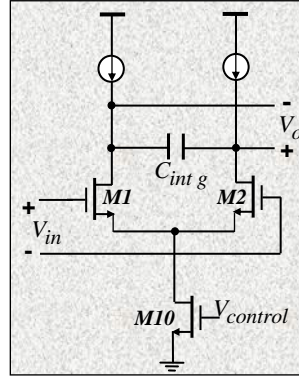
$$= 2 \left( \frac{1}{2} \mu C_{ox} \frac{W}{L} I_d \right)^{1/2}$$

*I<sub>d</sub> varied via V<sub>control</sub>*  
 $\rightarrow$  *g<sub>m</sub> tunable via V<sub>control</sub>*

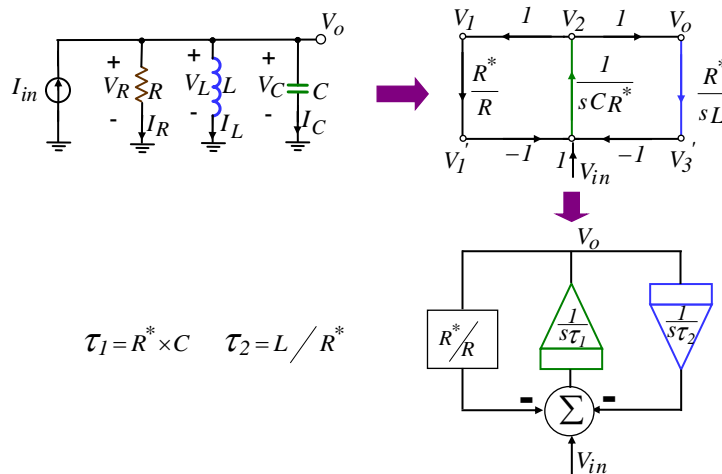


## Gm-C Filters 2<sup>nd</sup> Order Gm-C Filter

- Use the Gm-cell to build a 2<sup>nd</sup> order bandpass filter



## 2<sup>nd</sup> Order Bandpass Filter



## 2nd Order Integrator-Based Bandpass Filter

$$\frac{V_{BP}}{V_{in}} = \frac{\tau_2 s}{\tau_1 \tau_2 s^2 + \beta \tau_2 s + 1}$$

$$\tau_1 = R^* \times C \quad \tau_2 = L / R^*$$

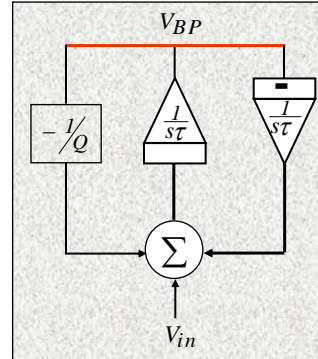
$$\beta = R^* / R$$

$$\omega_0 = 1 / \sqrt{\tau_1 \tau_2} = 1 / \sqrt{L C}$$

$$Q = 1 / \beta \times \sqrt{\tau_1 / \tau_2}$$

From matching point of view desirable:

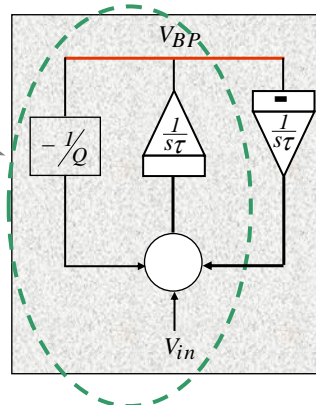
$$\tau_1 = \tau_2 = \tau = \frac{1}{\omega_0} \rightarrow Q = R / R^*$$



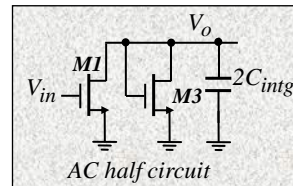
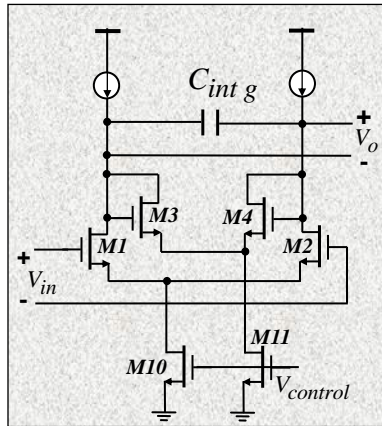
## 2nd Order Integrator-Based Bandpass Filter

First implement this part  
With transfer function:

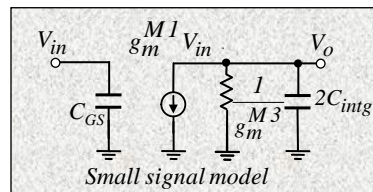
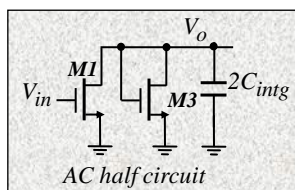
$$\frac{V_0}{V_{in}} = \frac{-1}{\frac{s}{\omega_0} + \frac{1}{Q}}$$



## Terminated Gm-C Integrator



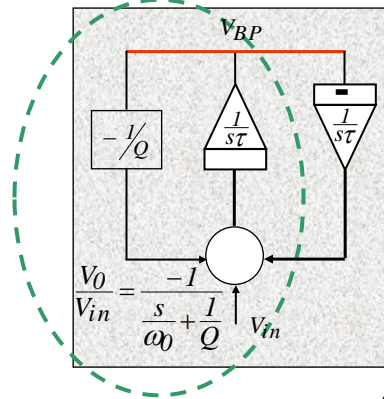
## Terminated Gm-C Integrator



$$\frac{V_o}{V_{in}} = \frac{-I}{s \frac{2C_{int} g}{g_m} + \frac{M3}{g_m}}$$

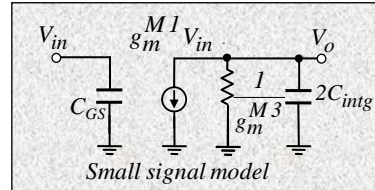
Compare to:  $\frac{V_o}{V_{in}} = \frac{-I}{s + \frac{I}{Q}}$

## Terminated Gm-C Integrator



$$\frac{V_0}{V_{in}} = \frac{-I}{\frac{s}{\omega_0} + \frac{1}{Q}}$$

$$\rightarrow \omega_0 = \frac{g_m^{M1}}{2C_{int}g} \quad \& \quad Q = \frac{g_m^{M1}}{g_m^{M3}}$$



$$\frac{V_o}{V_{in}} = \frac{-I}{\frac{s \times 2C_{int}g}{g_m^{M1}} + \frac{g_m^{M3}}{g_m^{M1}}}$$

Question: How to define Q accurately?

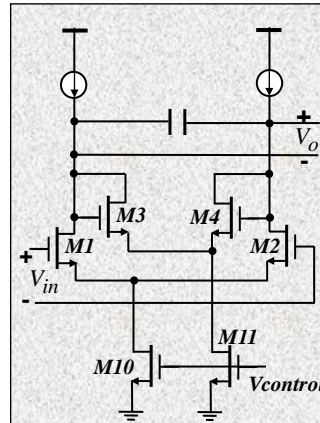
## Terminated Gm-C Integrator

$$g_m^{M1} = 2 \left( \frac{1}{2} \mu C_{ox} \frac{W_{M1}}{L_{M1}} I_d^{M1} \right)^{1/2}$$

$$g_m^{M3} = 2 \left( \frac{1}{2} \mu C_{ox} \frac{W_{M3}}{L_{M3}} I_d^{M3} \right)^{1/2}$$

Let us assume equal channel lengths for M1, M3 then:

$$\frac{g_m^{M1}}{g_m^{M3}} = \left( \frac{I_d^{M1}}{I_d^{M3}} \times \frac{W_{M1}}{W_{M3}} \right)^{1/2}$$



## Terminated Gm-C Integrator

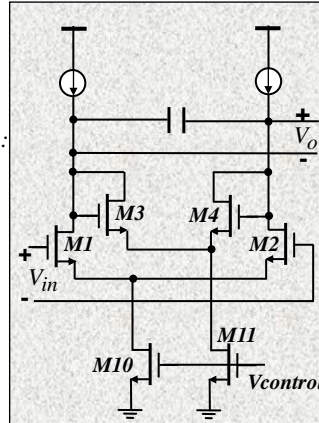
Note that:

$$\frac{I_d^{M1}}{I_d^{M3}} = \frac{I_d^{M10}}{I_d^{M11}}$$

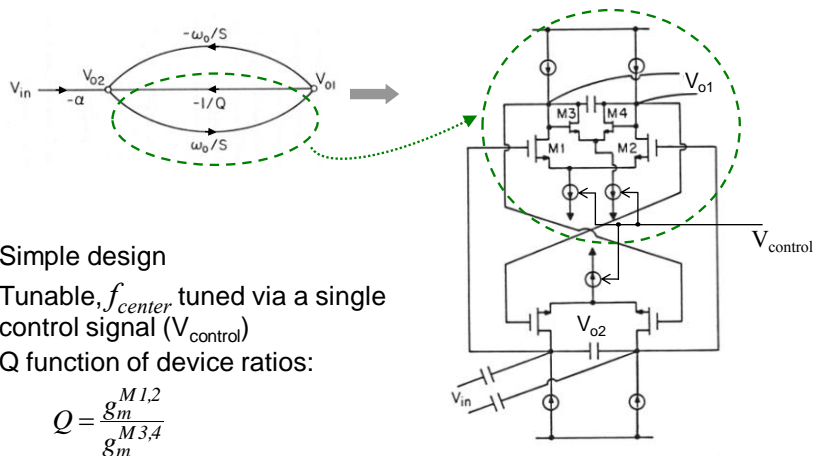
Assuming equal channel lengths for M10, M11:

$$\frac{I_d^{M10}}{I_d^{M11}} = \frac{W_{M10}}{W_{M11}}$$

$$\rightarrow \frac{g_m^{M1}}{g_m^{M3}} = \left( \frac{W_{M10}}{W_{M11}} \times \frac{W_{M1}}{W_{M3}} \right)^{1/2}$$



## 2nd Order Gm-C Filter



- Simple design
- Tunable,  $f_{center}$  tuned via a single control signal ( $V_{control}$ )
- Q function of device ratios:

$$Q = \frac{g_m^{M1,2}}{g_m^{M3,4}}$$

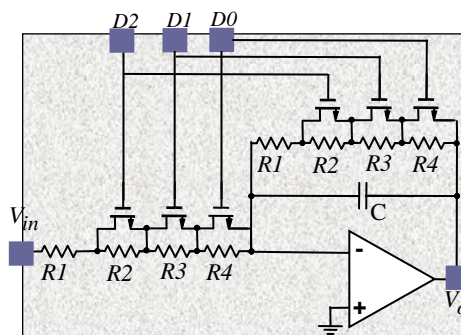
## Continuous-Time Filter Frequency Tuning Techniques

- Component trimming
- Automatic on-chip filter tuning
  - Continuous tuning
    - Master-slave tuning
  - Periodic off-line tuning
    - Systems where filter is followed by ADC & DSP, existing hardware can be used to periodically update filter freq. response

## Example: Tunable Opamp-RC Filter

Post manufacturing:

- Usually at wafer-sort tuning performed
- Measure -3dB frequency
  - If frequency too high decrement D to D-1
  - If frequency too low increment D to D+1
  - If frequency within 10% of the desired corner freq. stop



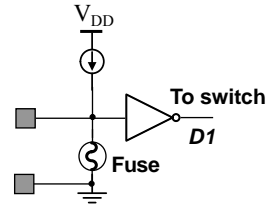
Not practical to require end-user to tune the filter  
→ Need to fix the adjustment at the factory



# Factory Trimming

- Factory component trimming

- Build fuses on-chip
  - Based on measurements @ wafer-sort blow fuses selectively by applying high current to the fuse
    - Expensive
    - Fuse regrowth problems!
    - Does not account for temp. variations & aging



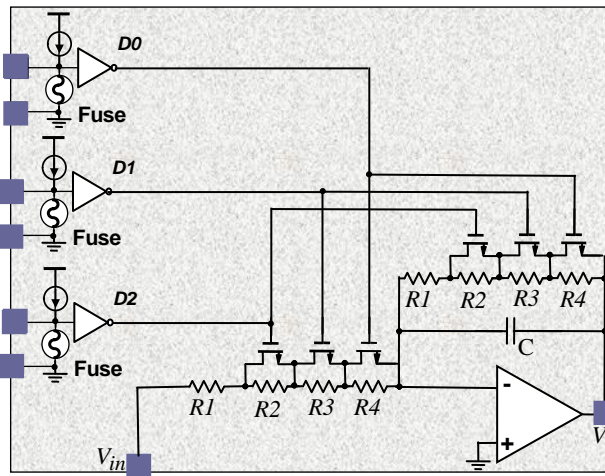
**Fuse not blown** →  $D1=1$   
**Fuse blown** →  $D1=0$

- Laser trimming

- Trim components or cut fuses by laser
  - Even more expensive
  - Does not account for temp. variations & aging

## Example: Tunable/Trimmable Opamp-RC Filter

D2	D1	D0	Rnom
1	1	1	7.2K
1	1	0	8.28K
1	0	1	9.37K
0	0	0	14.8K



## Automatic Frequency Tuning

- By adding additional circuitry to the main filter circuit
  - Have the filter critical frequency automatically tuned
    - ☺ Expensive trimming avoided
    - ☺ Accounts for critical frequency variations due to temperature, supply voltage, and effect of aging
    - ☺ Additional hardware, increased Si area & power dissipation & reference signal feed-thru

## Master-Slave Automatic Frequency Tuning

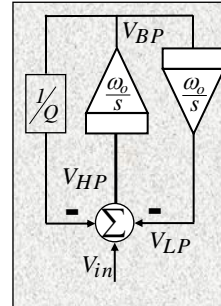
- Following facts used in this scheme:
  - Use a replica of the main filter or its main building block in the tuning circuitry
  - The replica is called the master and the main filter is named the slave
  - Place the replica in close proximity of the main filter to ensure good matching between master & slave
  - Use the tuning signal generated to tune the replica, to also tune the main filter
  - In the literature, this scheme is called *master-slave* tuning!

## Master-Slave Frequency Tuning 1-Reference Filter (VCF)

- Use a biquad built with replica of main filter integrator for master filter (VCF)
- Utilize the fact that @ the frequency  $f_o$ , the lowpass (or highpass) outputs signal should be 90 degree out of phase wrt to input

$$\frac{V_{LP}}{V_{in}} = \frac{1}{\frac{s^2}{\omega_o^2} + \frac{s}{Q\omega_o} + 1} \bigg|_{\omega = \omega_o} = -jQ \rightarrow \phi = -90^\circ$$

- Apply a sinusoid at the desired  $f_o^{\text{desired}}$
- Compare the phase of LP output versus input
- Based on the phase difference:
  - Increase or decrease filter critical freq.



## Master-Slave Frequency Tuning 1-Reference Filter (VCF)

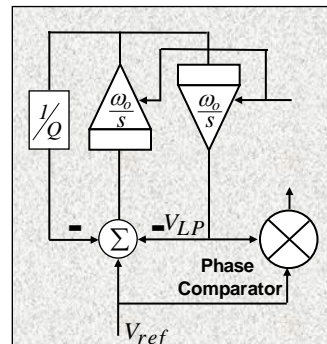
$$V_{ref} = A \sin(\omega t)$$

$$V_{LP} = A_2 \sin(\omega t + \phi)$$

$$V_{ref} \times V_{LP} = A_2 A \sin(\omega t) \sin(\omega t + \phi)$$

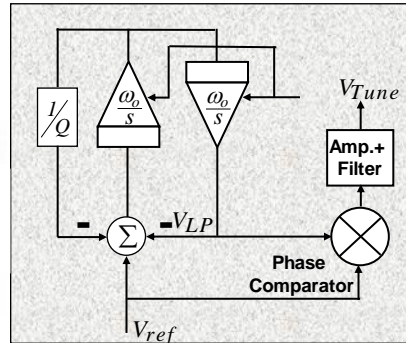
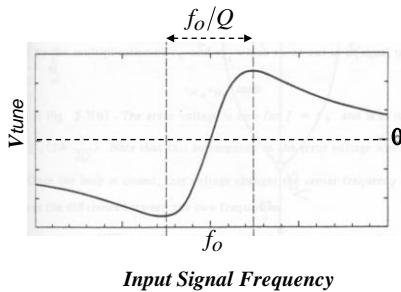
$$V_{ref} \times V_{LP} = \underbrace{\frac{A_2 A}{2} \cos \phi}_{\text{Note that this term is 0 only when the incoming signal is at exactly the filter -3dB frequency}} - \underbrace{\frac{A_2 A}{2} \cos(2\omega t + \phi)}_{\text{Filter Out}}$$

Note that this term is=0 only when the incoming signal is at exactly the filter -3dB frequency



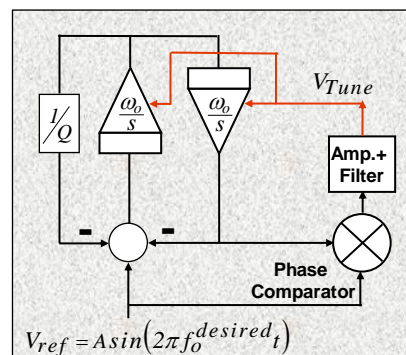
## Master-Slave Frequency Tuning 1-Reference Filter (VCF)

$$V_{tune} \approx -K \times V_{ref}^{rms} \times V_{LP}^{rms} \times \cos \phi$$

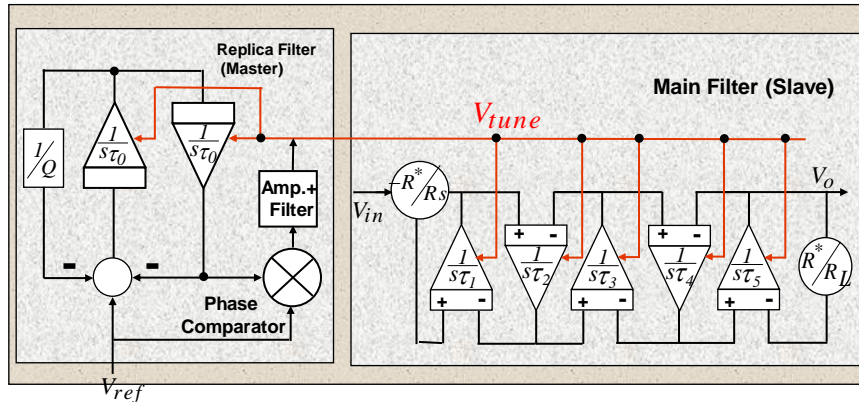


## Master-Slave Frequency Tuning 1-Reference Filter (VCF)

- By closing the loop, feedback tends to drive the error voltage ( $V_{Tune}$ ) to zero.
  - Locks  $f_o$  to  $f_o^{desired}$ , the critical frequency of the filter to the accurate reference frequency
- Typically the reference frequency is provided by a crystal oscillator with accuracies in the order of few ppm



## Master-Slave Frequency Tuning 1-Reference Filter (VCF)



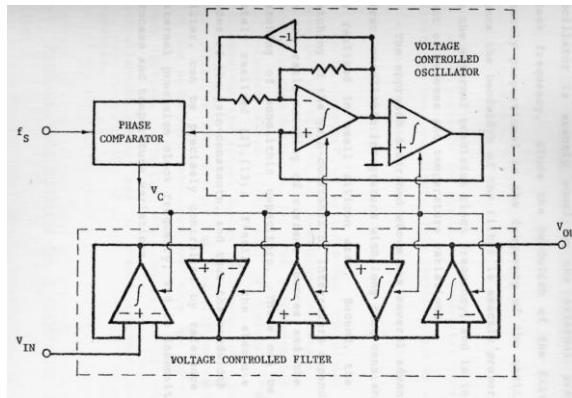
Ref: H. Khorrabadi and P.R. Gray, "High Frequency CMOS continuous-time filters," IEEE Journal of Solid-State Circuits, Vol.-SC-19, No. 6, pp.939-948, Dec. 1984.

## Master-Slave Frequency Tuning 1-Reference Filter (VCF)

- Issues to be aware of:
  - Input reference tuning signal needs to be sinusoid → Disadvantage since clocks are usually available as square waveform
  - Reference signal feed-through via parasitic coupling to the output of the filter can limit filter dynamic range (reported levels of about  $100\mu V_{rms}$ )
  - Ref. signal feed-through is a function of:
    - Reference signal frequency with respect to filter passband
    - Filter topology
    - Care in the layout
    - Fully differential topologies beneficial

## Master-Slave Frequency Tuning 2- Reference Voltage-Controlled-Oscillator (VCO)

- Instead of VCF a voltage-controlled-oscillator (VCO) is used
- VCO made of replica integrator used in main filter
- Tuning circuit operates exactly as a conventional phase-locked loop (PLL)
- Tuning signal used to tune main filter

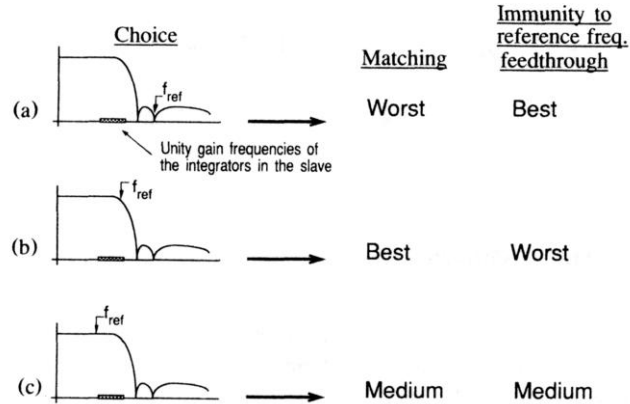


Ref: K.S. Tan and P.R. Gray, "Fully integrated analog filters using bipolar FET technology," IEEE, J. Solid-State Circuits, vol. SC-13, no.6, pp. 814-821, December 1978..

## Master-Slave Frequency Tuning 2- Reference Voltage-Controlled-Oscillator (VCO)

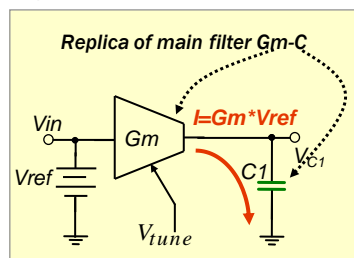
- Issues to be aware of:
  - Design of stable & repeatable oscillator challenging
  - VCO operation should be limited to the linear region of the integrator or else the operation loses accuracy (e.g. large signal transconductance versus small signal in a gm-C filter)
  - Limiting the VCO signal range to the linear region not a trivial design issue
  - In the case of VCF based tuning ckt, there was only ref. signal feedthrough. In this case, there is also the feedthrough of the VCO signal!!
  - Advantage over VCF based tuning → Reference input signal square wave (not sin.)

## Master-Slave Frequency Tuning Choice of Ref. Frequency wrt Feedthrough Immunity



Ref: V. Gopinathan, et. al, "Design Considerations for High-Frequency Continuous-Time Filters and Implementation of an Antialiasing Filter for Digital Video," *IEEE JSSC*, Vol. SC-25, no. 6 pp. 1368-1378, Dec. 1990.

## Master-Slave Frequency Tuning 3-Reference Integrator Locked to Reference Frequency



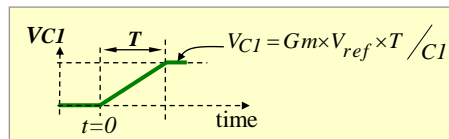
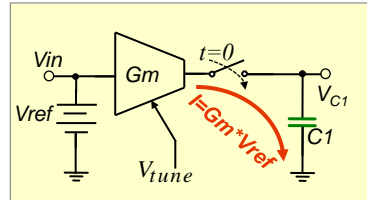
- Replica of main filter integrator e.g. Gm-C building block used
- Utilizes the fact that a DC voltage source connected to the input of the Gm cell generates a constant current at the output proportional to the transconductance and the voltage reference

$$I = Gm \cdot Vref$$

## Reference Integrator Locked to Reference Frequency

• Consider the following sequence:

- Integrating capacitor is fully discharged @  $t=0$
- At  $t=0$  the capacitor is connected to the output of the Gm cell then:



$$Q_{C1} = V_{C1} \times C1 = Gm \times V_{ref} \times T$$

$$\rightarrow V_{C1} = Gm \times V_{ref} \times T / C1$$

## Reference Integrator Locked to Reference Frequency

Since at the end of the period T:

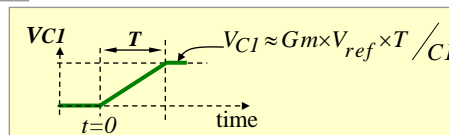
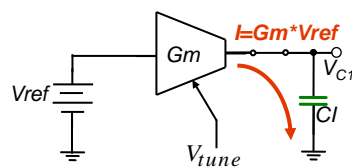
$$V_{C1} \approx Gm \times V_{ref} \times T / C1$$

If  $V_{C1}$  is forced to be equal to  $V_{ref}$  then:

$$\frac{C1}{Gm} = T = \frac{N}{f_{clk}}$$

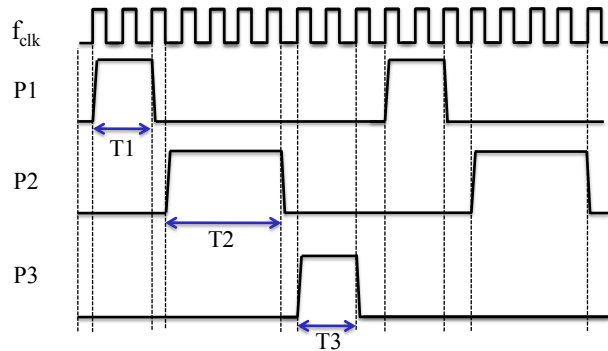
How do we manage to force  $V_{C1} = V_{ref}$ ?

→ Use feedback!!



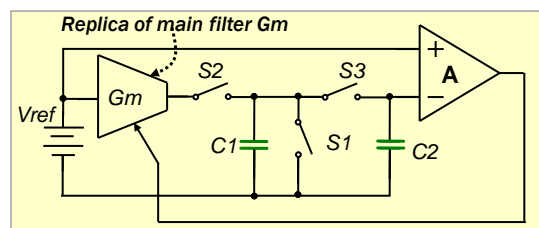


## Reference Integrator Locked to Reference Frequency Clocking Scheme

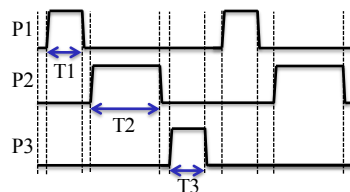


- Three clock phase operation
- Non-overlapping signals P1, P2, P3 derived from a master clock ( $f_{\text{clk}}$ )
- Note:  $T2=4/f_{\text{clk}}$

## Reference Integrator Locked to Reference Frequency

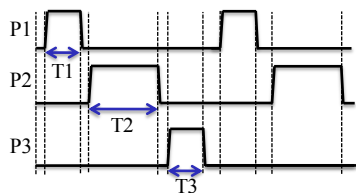
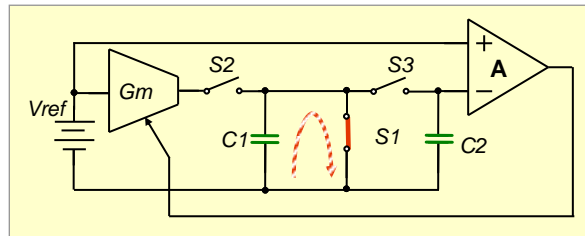


- Three clock phase operation
- To analyze  $\rightarrow$  study one phase at a time



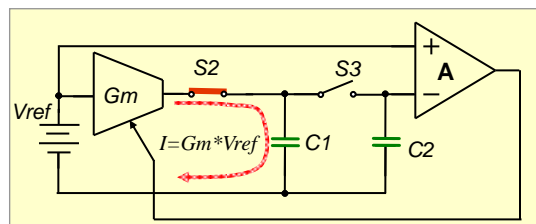
Ref: A. Durham, J. Hughes, and W. Redman-White, "Circuit Architectures for High Linearity Monolithic Continuous-Time Filtering," *IEEE Transactions on Circuits and Systems*, pp. 651-657, Sept. 1992.

Reference Integrator Locked to Reference Frequency  
P1 high  $\rightarrow$  S1 closed

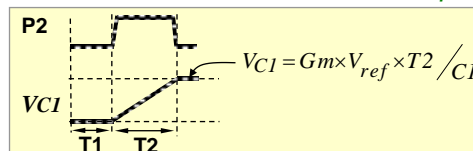


$C1 \rightarrow$  discharged  $\rightarrow V_{C1}=0$   
 $C2 \rightarrow$  retains its previous charge

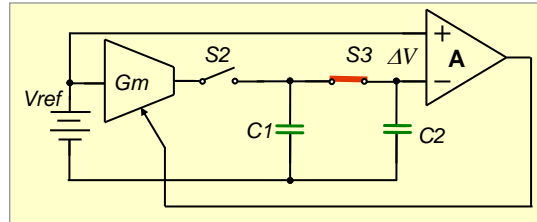
Reference Integrator Locked to Reference Frequency  
P2 high  $\rightarrow$  S2 closed



$C1 \rightarrow$  charged with constant current:  $I = Gm * V_{ref}$   
 $C2 \rightarrow$  retains its previous charge



Reference Integrator Locked to Reference Frequency  
 P3 high → S3 closed



*C1 charge shares with C2*

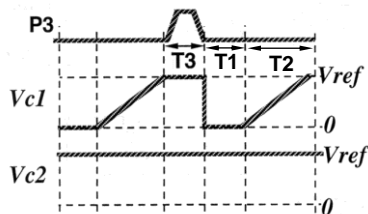
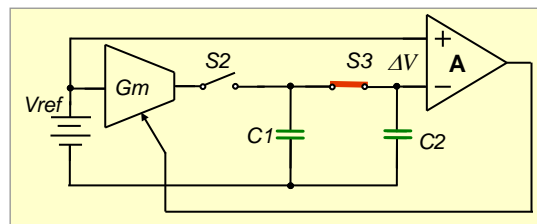
$$V_{C1}^{T2} C1 + V_{C2}^{T2} C2 = (C1 + C2) V_{C1,2}^{T3}$$

$$V_{C1,2}^{T3} = V_{C1}^{T2} \frac{C1}{C1 + C2} + V_{C2}^{T2} \frac{C2}{C1 + C2}$$

*Few cycles following startup system approaches steady state:*

$$V_{C1,2}^{T3} = V_{C1}^{T2} = V_{C2}^{T2}$$

Reference Integrator Locked to Reference Frequency  
 P3 high → S3 closed



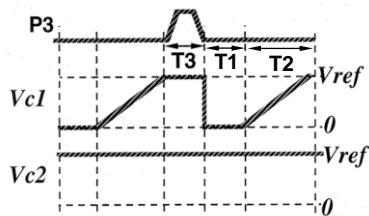
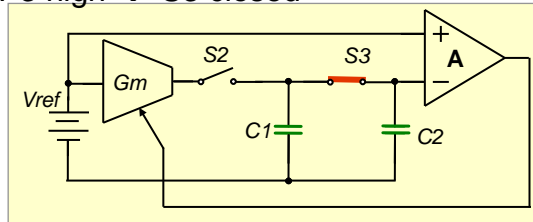
*C1 charge shares with C2*  
*Few cycles following startup*  
*Assuming A is large, feedback forces:*

$$\Delta V \rightarrow 0$$

$$\rightarrow V_{C2} = V_{ref}$$

## Reference Integrator Locked to Reference Frequency

P3 high  $\rightarrow$  S3 closed



$$V_{C1} = V_{C2} = V_{ref}$$

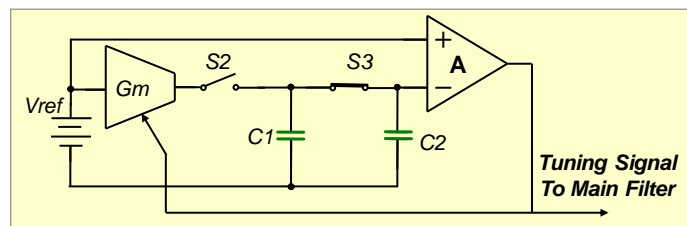
$$\text{since: } V_{C1} = G_m \times V_{ref} \times T_2 / C_1$$

$$\text{then: } V_{ref} = G_m \times V_{ref} \times T_2 / C_1$$

$$\text{or: } \frac{C_1}{G_m} = T_2 = N / f_{clk}$$

## Summary

### Replica Integrator Locked to Reference Frequency



Feedback forces Gm to assume a value so that :

- Integrator time constant locked to an accurate frequency
- Tuning signal used to adjust the time constant of the main filter integrators

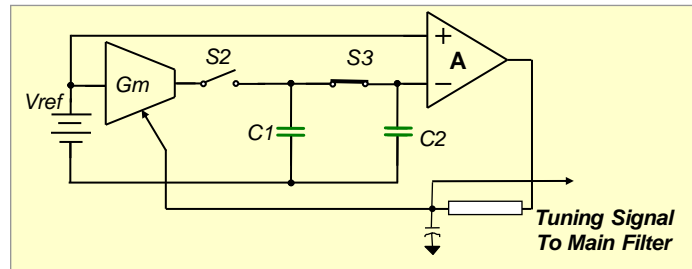
$$\tau_{intg} = \frac{C_1}{G_m} = N / f_{clk}$$

or

$$\omega_0^{intg} = \frac{G_m}{C_1} = f_{clk} / N$$

## Issues

### 1- Loop Stability

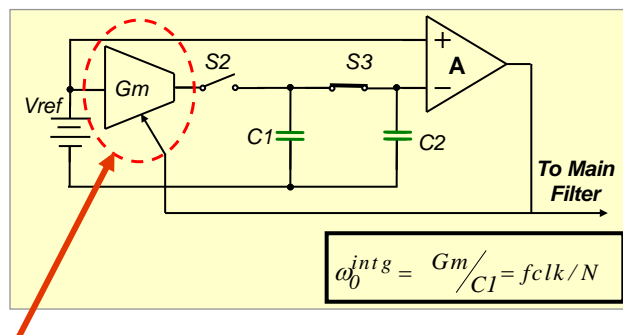


- Note: Need to pay attention to loop stability
  - ✓ C1 chosen to be smaller than C2 – tradeoff between stability and speed of lock acquisition
  - ✓ Lowpass filter at the output of amplifier (A) helps stabilize the loop

## Issues

### 2- GM-Cell DC Offset Induced Error

Problems to be aware of:



→ Tuning error due to master integrator DC offset

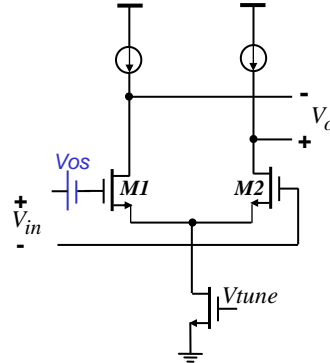
## Issues Gm Cell DC Offset

What is DC offset?

Simple example:

For the differential pair shown here, mismatch in input device or load characteristics would cause DC offset:  
 $\rightarrow V_o = 0$  requires a non-zero input voltage  
 $\rightarrow V_o = 0$  requires a non-zero input voltage

Offset could be modeled as a small DC voltage source at the input for which with shorted inputs  $\rightarrow V_o = 0$



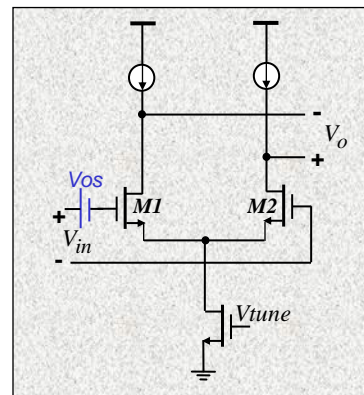
**Example: Differential Pair**

## Simple Gm-Cell DC Offset

Mismatch associated with the diff. pair:  
 M1 & M2  
 $\rightarrow$  DC offset

$$V_{os} = (V_{th1} - V_{th2}) - \frac{1}{2} V_{ov1,2} \frac{\Delta(W/L)_{M1,2}}{(W/L)_{M1,2}}$$

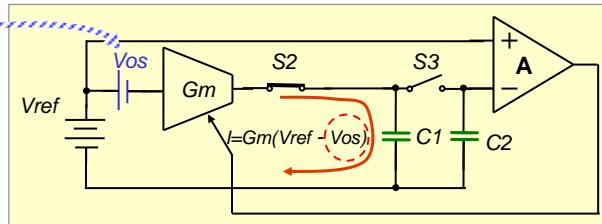
Assuming offset due to load device mismatch is negligible



Ref: Gray, Hurst, Lewis, Meyer, *Analysis & Design of Analog Integrated Circuits*, Wiley 2001, page 335

## Gm-Cell Offset Induced Error

Voltage source  
representing  
DC offset



- Effect of Gm-cell DC offset:

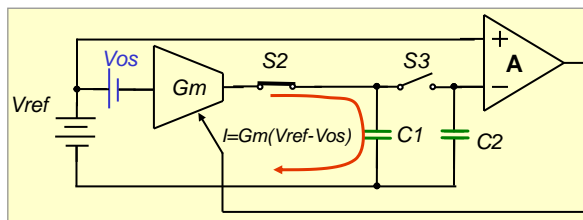
$$V_{C1} = V_{C2} = V_{ref}$$

$$\text{Ideal: } V_{C1} = Gm \times V_{ref} \times T2 / C1$$

$$\text{with offset: } V_{C1} = Gm \times (V_{ref} - V_{os}) \times T2 / C1$$

$$\text{or: } \frac{C1}{Gm} = T2 \left( 1 - \frac{V_{os}}{V_{ref}} \right)$$

## Gm-Cell Offset Induced Error



- Example:

$$\frac{C1}{Gm} = T2 \left( 1 - \frac{V_{os}}{V_{ref}} \right) \quad f_{critical} \propto \frac{Gm}{C1}$$

$$\text{for } \frac{V_{os}}{V_{ref}} = 1/10$$

10% error in tuning!